

# Ultralow Distortion, Wide Bandwidth Voltage Feedback Op Amps

## AD9631/AD9632

**FEATURES** Wide Bandwidth AD9631, G = +1AD9632, G = +2**Small Signal** 320 MHz 250 MHz Large Signal (4 V p-p) 175 MHz 180 MHz Ultralow Distortion (SFDR), Low Noise -113 dBc Typ @ 1 MHz -95 dBc Typ @ 5 MHz -72 dBc Typ @ 20 MHz 46 dBm Third Order Intercept @ 25 MHz 7.0 nV/√Hz Spectral Noise Density **High Speed** Slew Rate 1300 V/µs Settling 16 ns to 0.01%, 2 V Step ±3 V to ±5 V Supply Operation

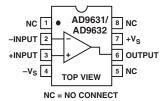
APPLICATIONS
ADC Input Driver
Differential Amplifiers
IF/RF Amplifiers
Pulse Amplifiers
Professional Video
DAC Current to Voltage
Baseband and Video Communications
Pin Diode Receivers
Active Filters/Integrators/Log Amps

17 mA Supply Current

#### GENERAL DESCRIPTION

The AD9631 and AD9632 are very high speed and wide bandwidth amplifiers. They are an improved performance alternative to the AD9621 and AD9622. The AD9631 is unity gain stable. The AD9632 is stable at gains of 2 or greater. Using a voltage feedback architecture, the AD9631/AD9632's exceptional settling time, bandwidth, and low distortion meet the requirements of many applications that previously depended on current feedback amplifiers. Its classical op amp structure works much more predictably in many designs.

PIN CONFIGURATION 8-Lead PDIP (N) and SOIC (R) Packages



A proprietary design architecture has produced an amplifier that combines many of the best characteristics of both current feedback and voltage feedback amplifiers. The AD9631 and AD9632 exhibit exceptionally fast and accurate pulse response (16 ns to 0.01%) as well as extremely wide small signal and large signal bandwidth and ultralow distortion. The AD9631 achieves –72 dBc at 20 MHz, and 320 MHz small signal and 175 MHz large signal bandwidths.

These characteristics position the AD9631/AD9632 ideally for driving flash as well as high resolution ADCs. Additionally, the balanced high impedance inputs of the voltage feedback architecture allow maximum flexibility when designing active filters.

The AD9631/AD9632 are offered in the industrial (-40°C to +85°C) temperature range. They are available in PDIP and SOIC.

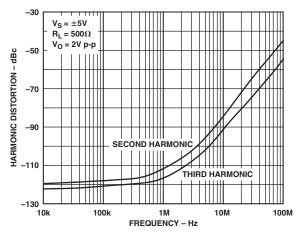


Figure 1. AD9631 Harmonic Distortion vs. Frequency, G = +1

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# AD9631/AD9632—SPECIFICATIONS

**ELECTRICAL CHARACTERISTICS** ( $\pm V_S = \pm 5 \text{ V}$ ;  $R_{LOAD} = 100 \Omega$ ;  $A_V = 1$  (AD9631);  $A_V = 2$  (AD9632), unless otherwise noted.)

		AD0(21A	A D0(22 A	
Parameter	Conditions	AD9631A Min Typ Max	AD9632A Min Typ Max	Unit
	Conditions	Will Typ Max	Willi Typ Max	Cilit
DYNAMIC PERFORMANCE				
Bandwidth (-3 dB)	77 - 0.437	220 220	100 250	3.677
Small Signal	$V_{OUT} \le 0.4 \text{ V p-p}$	220 320	180 250	MHz
Large Signal <sup>1</sup> Bandwidth for 0.1 dB Flatness	$V_{OUT} = 4 \text{ V p-p}$	150 175	155 180	MHz
bandwidth for 0.1 db Flatness	$V_{OUT} = 300 \text{ mV p-p}$ AD9631, $R_F = 140 \Omega$ ;	130	130	MHz
	AD9631, $R_F = 140 \Omega_2$ , AD9632, $R_F = 425 \Omega$	150	150	WILLS
Slew Rate, Average ±	$V_{OUT} = 4 \text{ V Step}$	1000 1300	1200 1500	V/µs
Rise/Fall Time	$V_{OUT} = 0.5 \text{ V Step}$	1.2	1.4	ns ns
	$V_{OUT} = 4 \text{ V Step}$	2.5	2.1	ns
Settling Time				
To 0.1%	$V_{OUT} = 2 \text{ V Step}$	11	11	ns
To 0.01%	$V_{OUT} = 2 \text{ V Step}$	16	16	ns
HARMONIC/NOISE PERFORMANCE				
Second Harmonic Distortion	2 V p-p; 20 MHz, $R_L = 100 Ω$	-64 -57	-54 -47	dBc
	$R_L = 500 \Omega$	-72 -65	-72 -65	dBc
Third Harmonic Distortion	2 V p-p; 20 MHz, $R_L$ = 100 Ω	-76 -69	-74 -67	dBc
	$R_L = 500 \Omega$	-81 -74	-81 -74	dBc
Third Order Intercept	25 MHz	46	41	dBm
Noise Figure	$R_S = 50 \Omega$	18	14	dB
Input Voltage Noise	1 MHz to 200 MHz	7.0	4.3	nV/√Hz
Input Current Noise	1 MHz to 200 MHz	2.5	2.0	pA/√Hz
Average Equivalent Integrated	0.1.1111	100		***
Input Noise Voltage	0.1 MHz to 200 MHz	100	60	μV rms
Differential Gain Error (3.58 MHz)	$R_{L} = 150 \Omega$ $R_{L} = 150 \Omega$	0.03 0.06 0.02 0.04	0.02 0.04 0.02 0.04	% Domes
Differential Phase Error (3.58 MHz) Phase Nonlinearity	DC to 100 MHz	1.1	1.1	Degree Degree
<u> </u>	DG to 100 WHIZ	1.1	1.1	Degree
DC PERFORMANCE <sup>2</sup> , $R_L = 150 \Omega$		2 10	2 5	***
Input Offset Voltage <sup>3</sup>	T. T.	3 10	2 5	mV
Officer Voltage Duife	$T_{MIN}$ – $T_{MAX}$	13	8	mV
Offset Voltage Drift Input Bias Current		$\begin{array}{cccc} \pm 10 \\ 2 & 7 \end{array}$	$\begin{array}{cccc} \pm 10 \\ 2 & 7 \end{array}$	μV/°C
input bias Current	$T_{MIN}$ - $T_{MAX}$	10	10	μΑ μΑ
Input Offset Current	1 MIN 1 MAX	0.1 3	0.1 3	μΑ
input onset ourient	$T_{MIN}-T_{MAX}$	5	5	μΑ
Common-Mode Rejection Ratio	$V_{CM} = \pm 2.5 \text{ V}$	70 90	70 90	dB
Open-Loop Gain	$V_{OUT} = \pm 2.5 \text{ V}$	46 52	46 52	dB
	$T_{MIN}-T_{MAX}$	40	40	dB
INPUT CHARACTERISTICS				
Input Resistance		500	500	kΩ
Input Capacitance		1.2	1.2	pF
Input Common-Mode Voltage Range		±3.4	±3.4	V
OUTPUT CHARACTERISTICS				
Output Voltage Range, $R_L = 150 \Omega$		±3.2 ±3.9	±3.2 ±3.9	V
Output Current		70	70	mA
Output Resistance		0.3	0.3	Ω
Short Circuit Current		240	240	mA
POWER SUPPLY				
Operating Range		±3.0 ±5.0 ±6.0	±3.0 ±5.0 ±6.0	V
Quiescent Current		17 18	16 17	mA
-	$T_{MIN}$ - $T_{MAX}$	21	20	mA
Power Supply Rejection Ratio	$T_{MIN}$ - $T_{MAX}$	50 60	56 66	dB
	<u>'</u>			

NOTES

<sup>&</sup>lt;sup>1</sup>See Absolute Maximum Ratings and Theory of Operation sections of this data sheet.

 $<sup>^{2}</sup>$ Measured at A<sub>V</sub> = 50.

<sup>&</sup>lt;sup>3</sup>Measured with respect to the inverting input.

Specifications subject to change without notice.

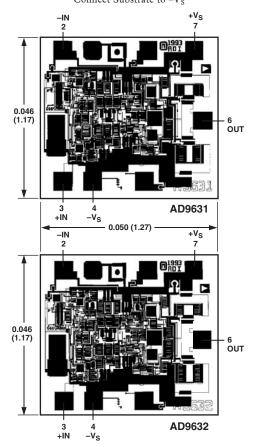
#### ABSOLUTE MAXIMUM RATINGS1

Supply Voltage $(+V_S \text{ to } -V_S)$
Voltage Swing × Bandwidth Product 550 V-MHz
Internal Power Dissipation <sup>2</sup>
Plastic Package (N)
Small Outline Package (R)
Input Voltage (Common Mode) $\pm V_S$
Differential Input Voltage±1.2 V
Output Short Circuit Duration
Observe Power Derating Curves
Storage Temperature Range N, R65°C to +125°C
Operating Temperature Range (A Grade)40°C to +85°C
Lead Temperature Range (Soldering 10 sec) 300°C

#### NOTES

#### **METALLIZATION PHOTO**

Dimensions shown in inches and (millimeters) Connect Substrate to  $-V_S$ 



#### MAXIMUM POWER DISSIPATION

The maximum power that can be safely dissipated by these devices is limited by the associated rise in junction temperature. The maximum safe junction temperature for plastic encapsulated devices is determined by the glass transition temperature of the plastic, approximately 150°C. Exceeding this limit temporarily may cause a shift in parametric performance due to a change in the stresses exerted on the die by the package. Exceeding a junction temperature of 175°C for an extended period can result in device failure.

While the AD9631 and AD9632 are internally short circuit protected, this may not be sufficient to guarantee that the maximum junction temperature (150°C) is not exceeded under all conditions. To ensure proper operation, it is necessary to observe the maximum power derating curves.

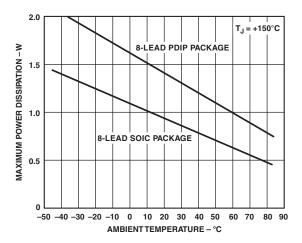


Figure 2. Maximum Power Dissipation vs. Temperature

#### **ORDERING GUIDE**

Model	Temperature Range	Package Description	Package Option
AD9631AN	−40°C to +85°C	PDIP	N-8
AD9631AR	−40°C to +85°C	SOIC	R-8
AD9631AR-REEL	−40°C to +85°C	SOIC	R-8
AD9631AR-REEL7	−40°C to +85°C	SOIC	R-8
AD9631CHIPS		Die	
AD9632AN	−40°C to +85°C	PDIP	N-8
AD9632AR	−40°C to +85°C	SOIC	R-8
AD9632AR-REEL	−40°C to +85°C	SOIC	R-8
AD9632AR-REEL7	−40°C to +85°C	SOIC	R-8

#### CAUTION

ESD (electrostatic discharge) sensitive device. Electrostatic charges as high as 4000 V readily accumulate on the human body and test equipment and can discharge without detection. Although the AD9631/AD9632 features proprietary ESD protection circuitry, permanent damage may occur on devices subjected to high energy electrostatic discharges. Therefore, proper ESD precautions are recommended to avoid performance degradation or loss of functionality.

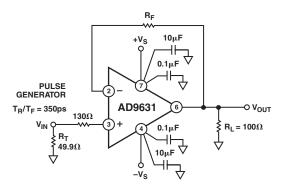


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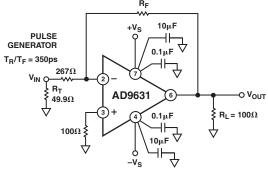
Stresses above those listed under Absolute Maximum Ratings may cause permanent damage to the device. This is a stress rating only; functional operation of the device at these or any other conditions above those indicated in the operational section of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

<sup>&</sup>lt;sup>2</sup> Specification is for device in free air: 8-Lead PDIP Package:  $\theta_{JA} = 90$ °C/W 8-Lead SOIC Package:  $\theta_{JA} = 140$ °C/W

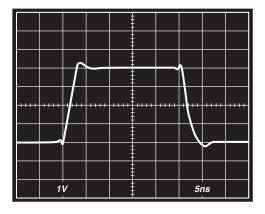
### **AD9631/AD9632—Typical Performance Characteristics**



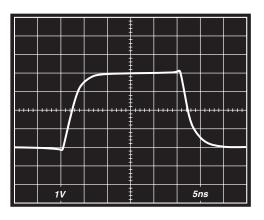
TPC 1. AD9631 Noninverting Configuration, G = +1



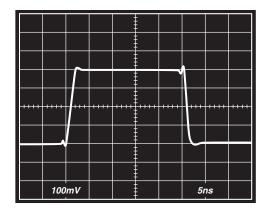
TPC 4. AD9631 Inverting Configuration, G = -1



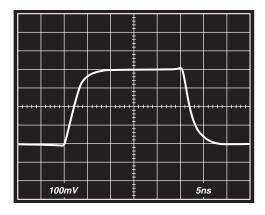
TPC 2. AD9631 Large Signal Transient Response;  $V_0 = 4 \ V \ p$ -p, G = +1,  $R_F = 250 \ \Omega$ 



TPC 5. AD9631 Large Signal Transient Response;  $V_O = 4 \text{ V p-p}, G = -1, R_F = R_{IN} = 267 \Omega$ 



TPC 3. AD9631 Small Signal Transient Response;  $V_O = 400 \text{ mV} \text{ p-p}, G = +1, R_F = 140 \Omega$ 



TPC 6. AD9631 Small Signal Transient Response;  $V_O = 400$  mV p-p, G = -1,  $R_F = R_{IN} = 267$   $\Omega$ 

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